

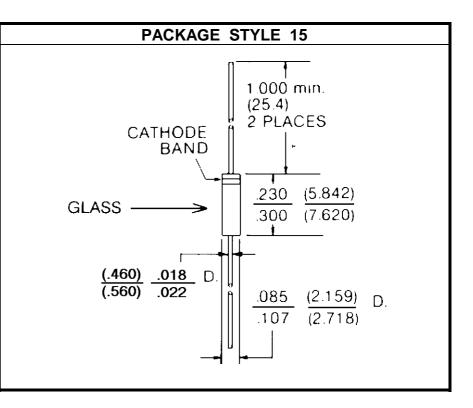
SILICON ABRUPT JUNCTION TUNING VARACTOR

DESCRIPTION:

The **AT6020** is an Epitaxial Silicon Abrupt Junction Microwave Tuning Varactor. This Device is Passivated With Silicon Dioxide Which Results in Very Low Leakage Current. The Capacitance Voltage Relationship Closely Approximates Square Law (n = 0.5).

MAXIMUM RATINGS

I _c	100 mA				
V_{CE}	70 V				
P _{DISS}	250 mW @ $T_c = 25 \ ^{\circ}C$				
TJ	-65 [°] C to +150 [°] C				
T _{STG}	-65 [°] C to +150 [°] C				



CHARACTERISTICS $T_{C} = 25 °C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V _B	I _R = 10 μA		70			V
CT	V _R = 4.0 V	f = 1.0 MHz	35.1	39.0	42.9	pF
ΔCT	$C_{T} = 0 V / C_{T} = 60 V$	f = 1.0 MHz	7.4			RATIO
Q	V _R = 4.0 V	f = 50 MHz	800			
Tc	V _R = 4.0 V				300	Ppm/ ^o C

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